

Polar3™ HiPerFET™ Power MOSFET

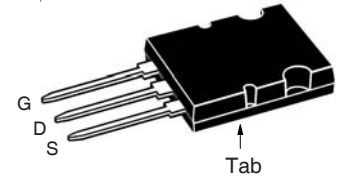
IXFB110N60P3

$V_{DSS} = 600V$
 $I_{D25} = 110A$
 $R_{DS(on)} \leq 56m\Omega$
 $t_{rr} \leq 250ns$

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier



PLUS264™



G = Gate D = Drain
 S = Source Tab = Drain

| Symbol | Test Conditions | Maximum Ratings | |
|------------|--------------------------------------------------------------------|-----------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | 600 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$ | 600 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ C$ | 110 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 275 | A |
| I_A | $T_C = 25^\circ C$ | 55 | A |
| E_{AS} | $T_C = 25^\circ C$ | 3 | J |
| dv/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$ | 35 | V/ns |
| P_D | $T_C = 25^\circ C$ | 1890 | W |
| T_J | | -55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | -55 ... +150 | $^\circ C$ |
| T_L | Maximum Lead Temperature for Soldering | 300 | $^\circ C$ |
| T_{SOLD} | Plastic Body for 10s | 260 | $^\circ C$ |
| F_C | Mounting Force | 30..120/6.7..27 | N/lb |
| Weight | | 10 | g |

Features

- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- Low $R_{DS(on)}$ and Q_G

Advantages

- Easy to Mount
- Space Savings

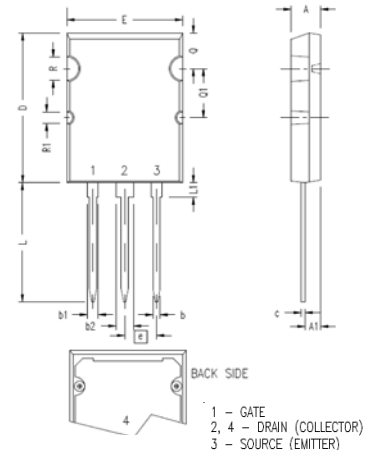
Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- Uninterrupted Power Supplies
- AC Motor Drives
- High Speed Power Switching Applications

| Symbol | Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---------------------------------------------------------------------|-----------------------|------|-----------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 3mA$ | 600 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 8mA$ | 3.0 | | 5.0 V |
| I_{GSS} | $V_{GS} = \pm 30V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$ | | | 50 μA 2.75 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 0.5 \cdot I_{DSS}$, Note 1 | | | 56 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|----------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------|------|--------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 20\text{V}, I_D = 55\text{A}$, Note 1 | 65 | 105 | S |
| C_{iss} | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ | | 18 | nF |
| C_{oss} | | | 1550 | pF |
| C_{rss} | | | 8 | pF |
| R_{Gi} | Gate Input Resistance | | 1.2 | Ω |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{DSS}$ $R_G = 1\Omega$ (External) | | 63 | ns |
| t_r | | | 30 | ns |
| $t_{d(off)}$ | | | 106 | ns |
| t_f | | | 15 | ns |
| $Q_{g(on)}$ | | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{DSS}$ | | 254 |
| Q_{gs} | | | 80 | nC |
| Q_{gd} | | | 68 | nC |
| R_{thJC} | | | | 0.066 $^\circ\text{C/W}$ |
| R_{thCS} | | 0.13 | | $^\circ\text{C/W}$ |

PLUS264™ (IXFB) Outline



| SYM | INCHES | | MILLIMETERS | |
|-----|----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .185 | .209 | 4.70 | 5.31 |
| A1 | .102 | .118 | 2.59 | 3.00 |
| b | .037 | .055 | 0.94 | 1.40 |
| b1 | .087 | .102 | 2.21 | 2.59 |
| b2 | .110 | .126 | 2.79 | 3.20 |
| c | .017 | .029 | 0.43 | 0.74 |
| D | 1.007 | 1.047 | 25.58 | 26.59 |
| E | .760 | .799 | 19.30 | 20.29 |
| e | .215 BSC | | 5.46 BSC | |
| L | .779 | .842 | 19.79 | 21.39 |
| L1 | .087 | .102 | 2.21 | 2.59 |
| Q | .240 | .256 | 6.10 | 6.50 |
| Q1 | .330 | .346 | 8.38 | 8.79 |
| ØR | .155 | .187 | 3.94 | 4.75 |
| ØR1 | .085 | .093 | 2.16 | 2.36 |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|----------|-------------------------------------------------------------------------------------------------|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| I_s | $V_{GS} = 0\text{V}$ | | | 110 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 440 A |
| V_{SD} | $I_F = 100\text{A}, V_{GS} = 0\text{V}$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 55\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$ | | | 250 ns |
| Q_{RM} | | | 1.6 | μC |
| I_{RM} | | | 14.0 | A |

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

| | | | | | | | | | |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

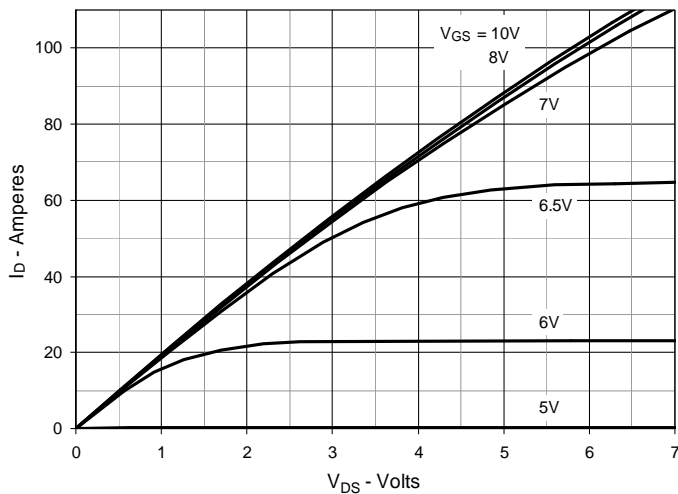
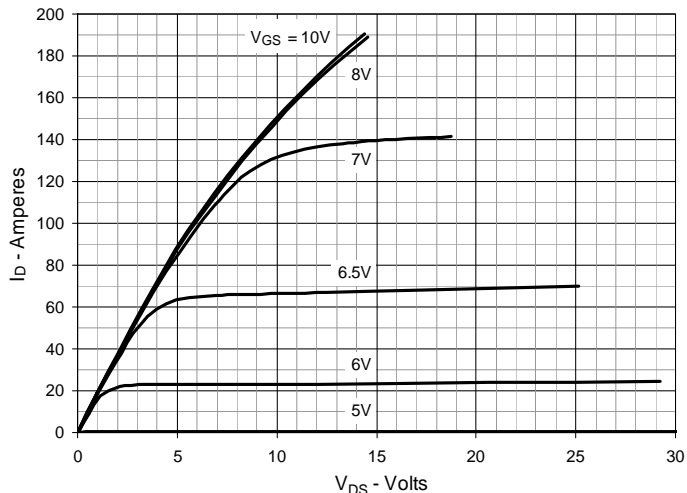
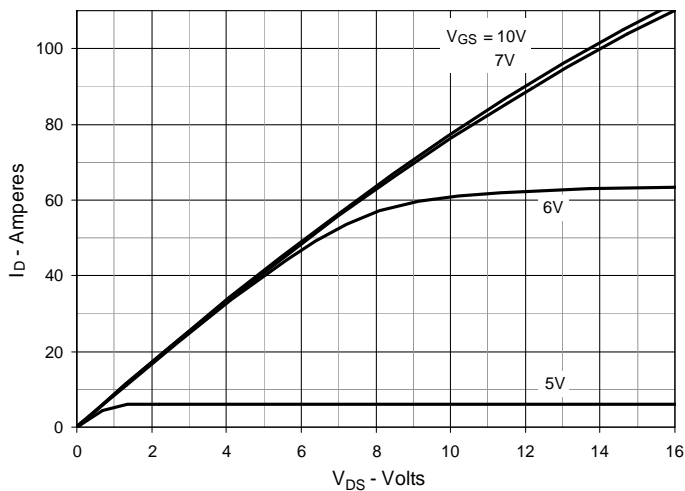
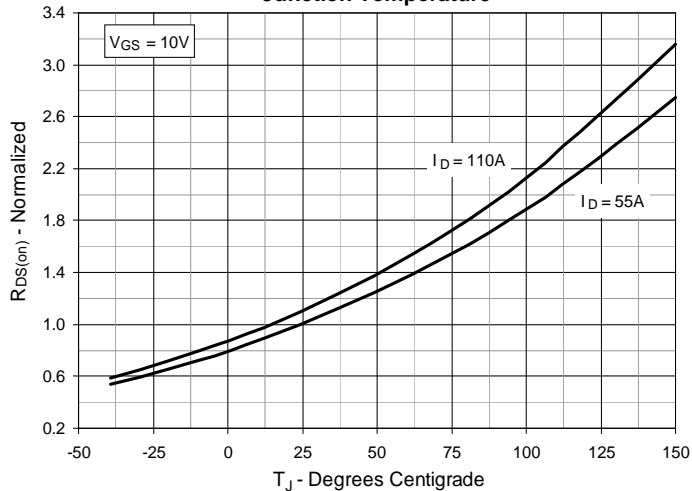
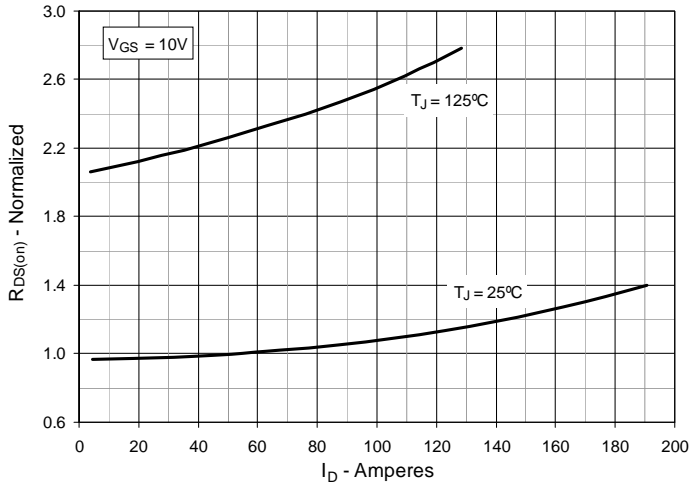
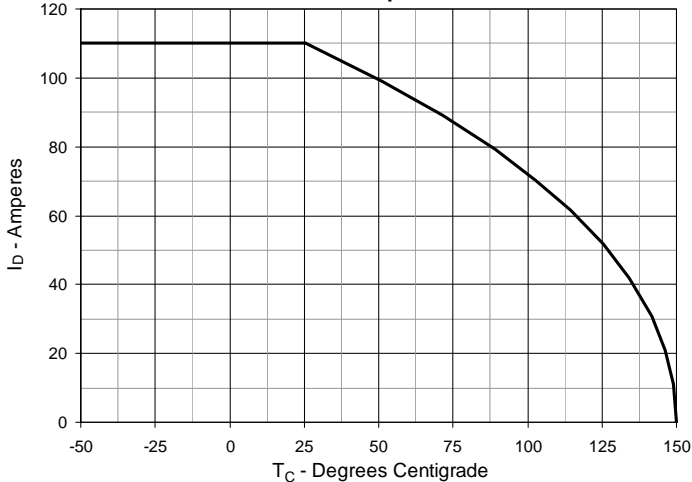
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 55\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 55\text{A}$ Value vs. Drain Current

Fig. 6. Maximum Drain Current vs. Case Temperature


Fig. 7. Input Admittance

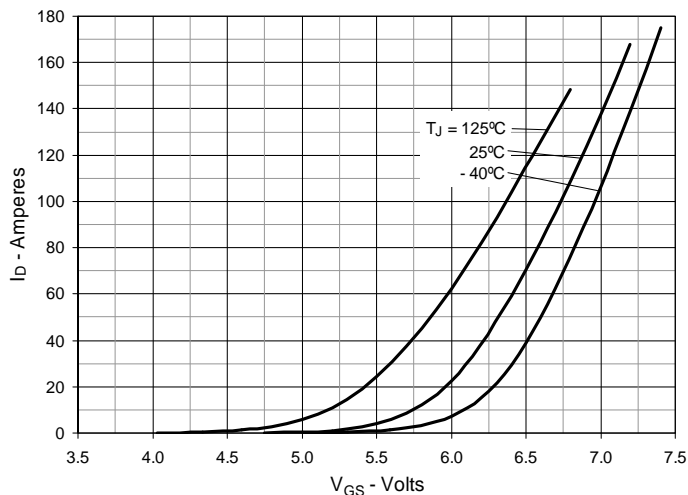


Fig. 8. Transconductance

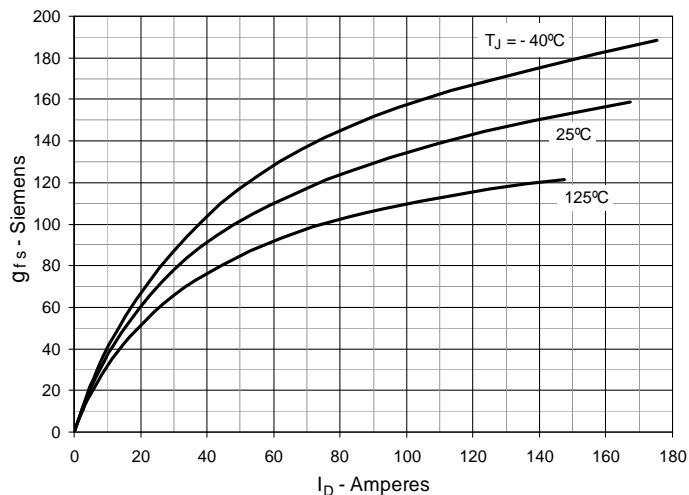


Fig. 9. Forward Voltage Drop of Intrinsic Diode

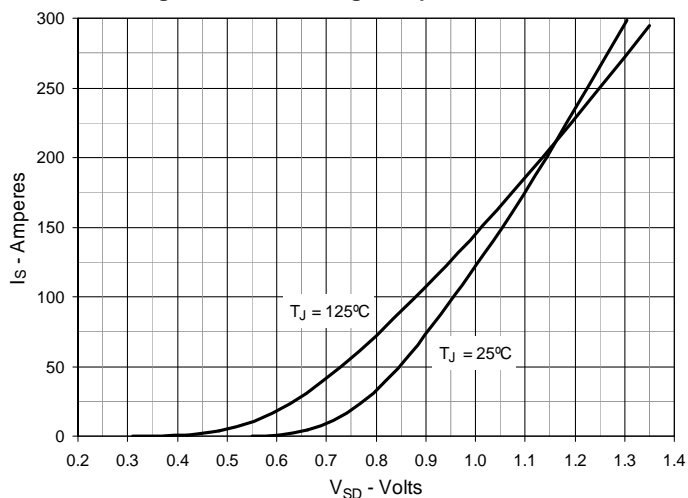


Fig. 10. Gate Charge

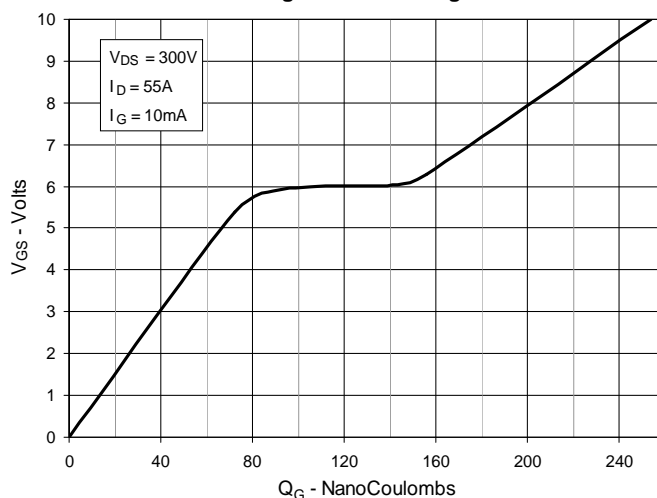


Fig. 11. Capacitance

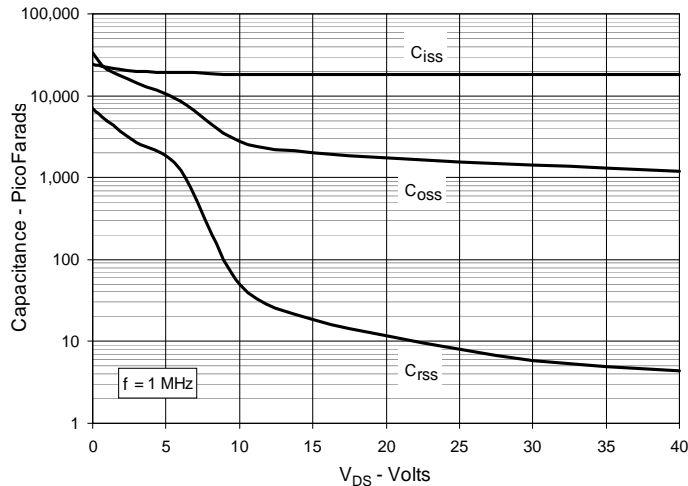


Fig. 12. Forward-Bias Safe Operating Area

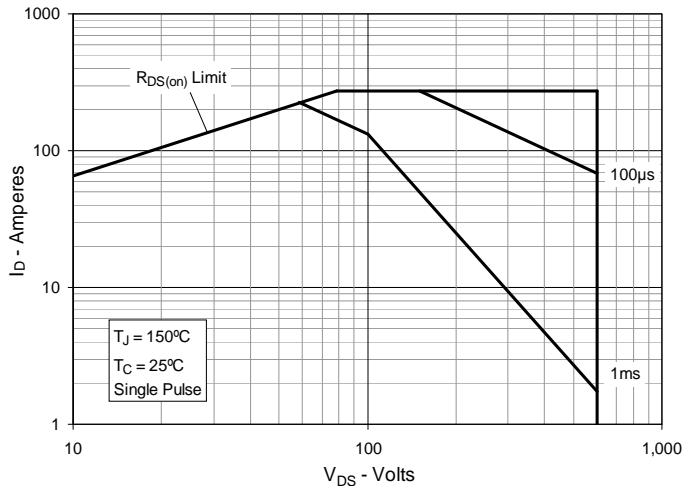
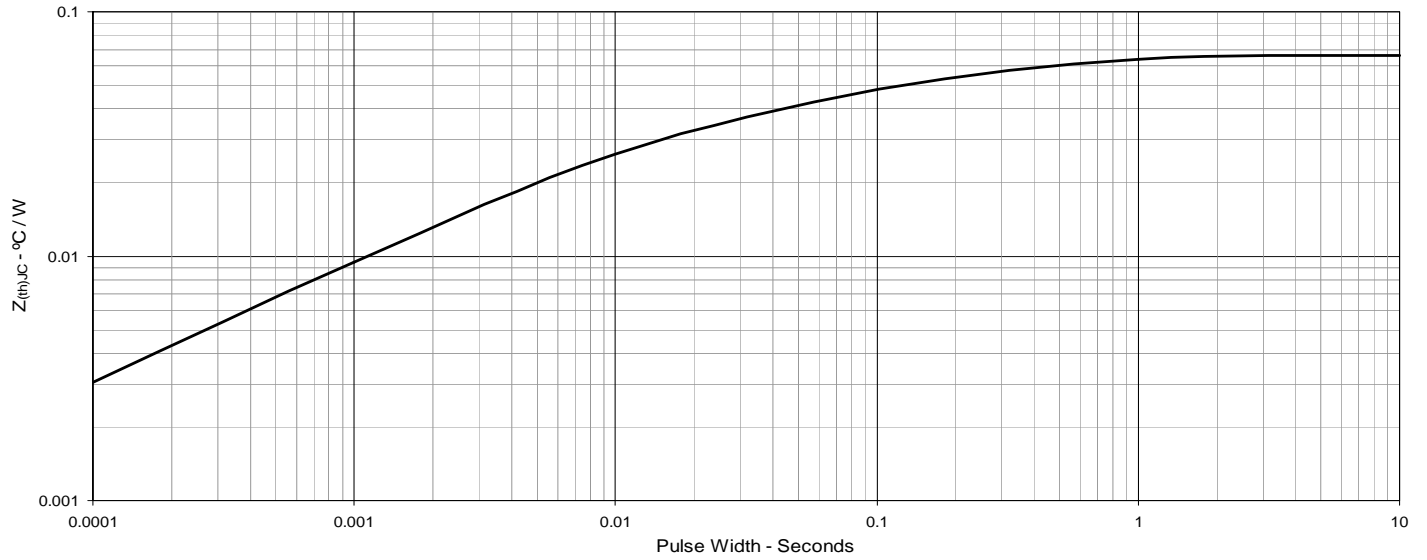


Fig. 13. Maximum Transient Thermal Impedance





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